

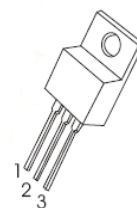
**TO-220-3L Plastic-Encapsulate MOSFETS****CJP12N65**

N-Channel Power MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D
650V	$0.7\Omega @ 10V$	12A

GENERAL DESCRIPTION

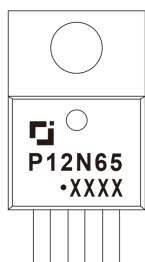
This advanced high voltage MOSFET is designed to stand high energy in the avalanche mode and switch efficiently. This new high energy device also offers a drain-to-source diode fast recovery time. Designed for high voltage, high speed switching applications such as power supplies, converters, power motor controls and bridge circuits.

TO-220-3L

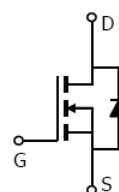
1. GATE
2. DRAIN
3. SOURCE

FEATURE

- High Current Rating
- Lower $R_{DS(on)}$
- Low Reverse Transfer Capacitance
- Fast Switching Capability
- Tighter V_{SD} Specifications
- Avalanche Energy Specified

MARKING

P12N65= Device code
Solid dot = Green molding compound device,
if none, the normal device
XXX=Code

Equivalent Circuit**Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	650	V
Gate-Source Voltage	V_{GSS}	± 30	
Continuous Drain Current	I_D	12	A
Pulsed Drain Current(note1)	I_{DM}	48	
Single Pulsed Avalanche Energy (note2)	E_{AS}	540	mJ
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 ~ +150	
Maximum lead temperature for soldering purposes , 1/8"from case for 5 seconds	T_L	260	

MOSFET ELECTRICAL CHARACTERISTICS

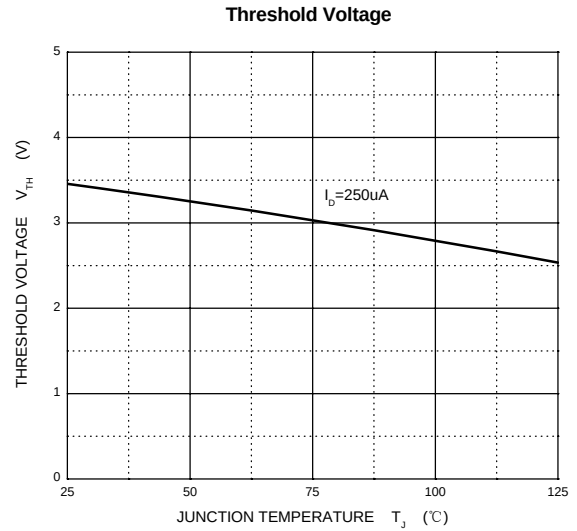
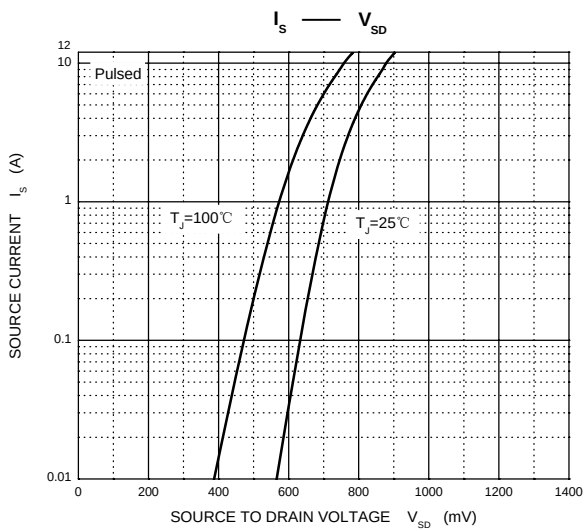
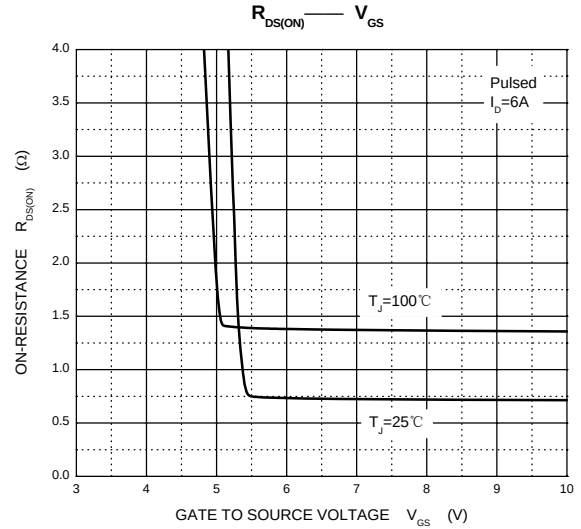
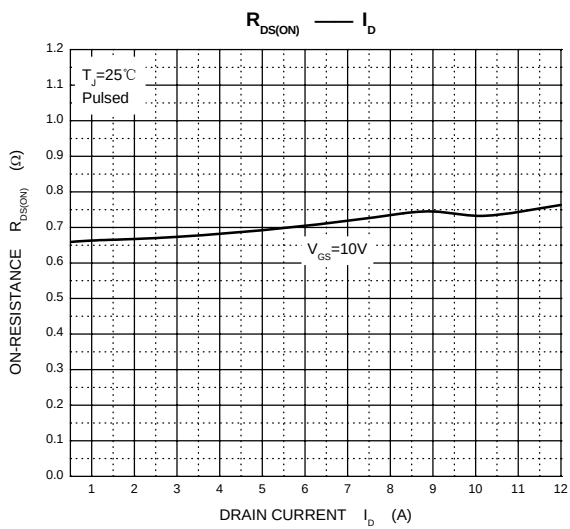
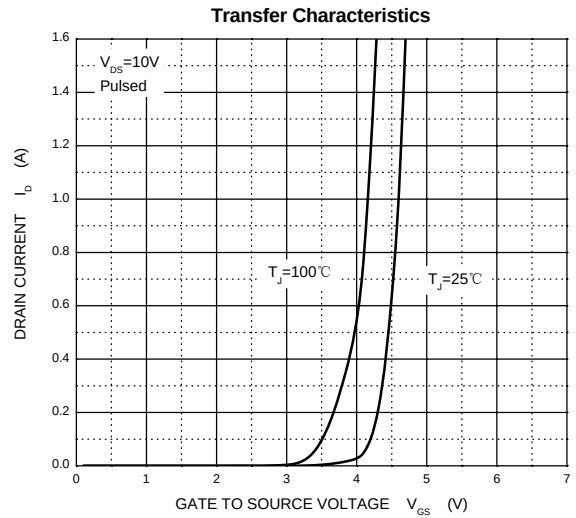
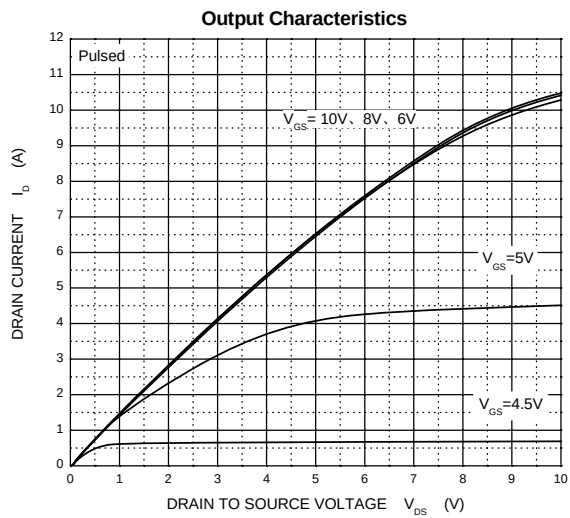
$T_a=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	650			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =650V, V _{GS} =0V			1	μA
Gate-body leakage current (note3)	I _{GSS}	V _{DS} =0V, V _{GS} =± 30V			± 100	nA
On characteristics (note3)						
Gate-threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.0	3.5	4.0	V
Static drain-source on-resistance	R _{DS(on)}	V _{GS} =10V, I _D =6A		0.7	0.85	Ω
Dynamic characteristics (note 4)						
Input capacitance	C _{iss}	V _{DS} =25V,V _{GS} =0V,f =1MHz		1800		pF
Output capacitance	C _{oss}			200		
Reverse transfer capacitance	C _{rss}			25		
Switching characteristics (note1,3 4)						
Total gate charge	Q _g	V _{DS} =520V,V _{GS} =10V,I _D =12A		42	54	nC
Gate-source charge	Q _{gs}			8.6		
Gate-drain charge	Q _{gd}			21		
Turn-on delay time	t _{d(on)}	V _{DD} =325V, V _{GS} =10V, R _G =4.7Ω, I _D =12A		30		ns
Turn-on rise time	t _r			90		
Turn-off delay time	t _{d(off)}			160		
Turn-off fall time	t _f			90		
Drain-Source Diode Characteristics						
Drain-source diode forward voltage(note3)	V _{SD}	V _{GS} = 0V, I _S =12A			1.4	V
Continuous drain-source diode forward current	I _S				12	A
Pulsed drain-source diode forward current	I _{SM}				48	A

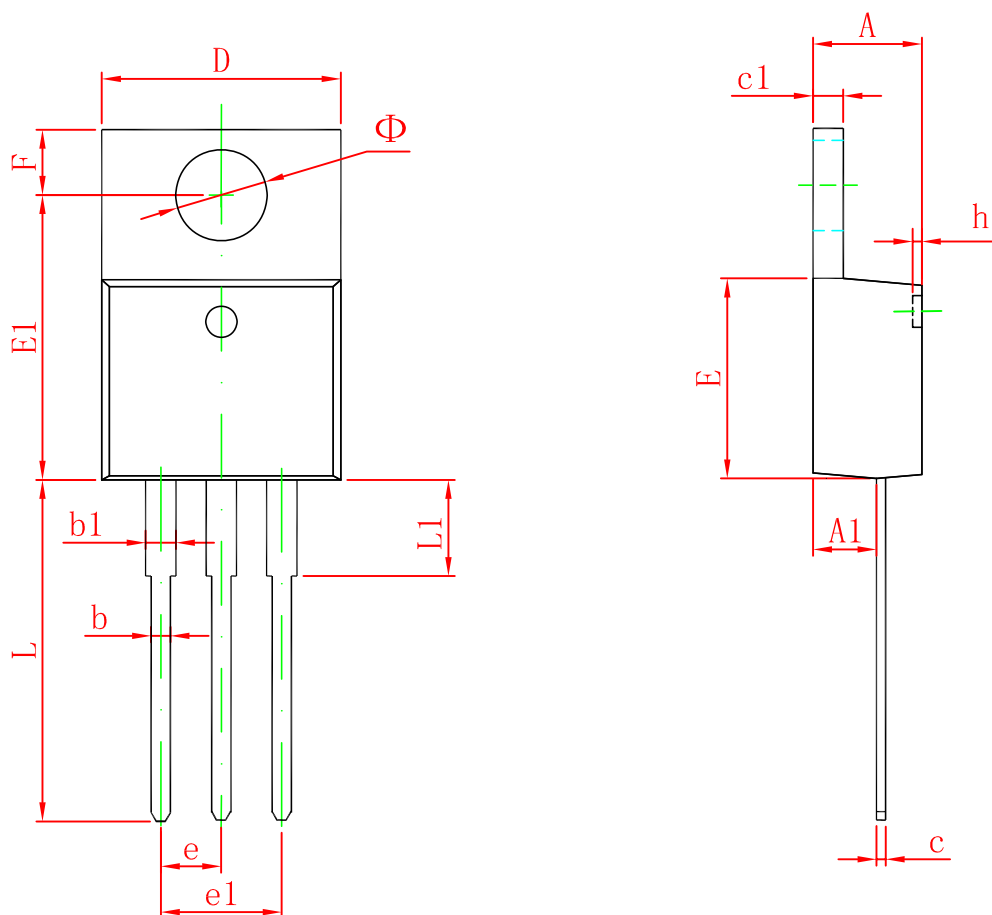
Notes :

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 7.5mH, I_{AS} = 12A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^{\circ}C$
3. Pulse Test : Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. These parameters have no way to verify.

Typical Characteristics



TO-220-3L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.470	4.670	0.176	0.184
A1	2.520	2.820	0.099	0.111
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
E1	12.060	12.460	0.475	0.491
e	2.540 TYP		0.100 TYP	
e1	4.980	5.180	0.196	0.204
F	2.590	2.890	0.102	0.114
h	0.000	0.300	0.000	0.012
L	13.400	13.800	0.528	0.543
L1	3.560	3.960	0.140	0.156
Φ	3.735	3.935	0.147	0.155